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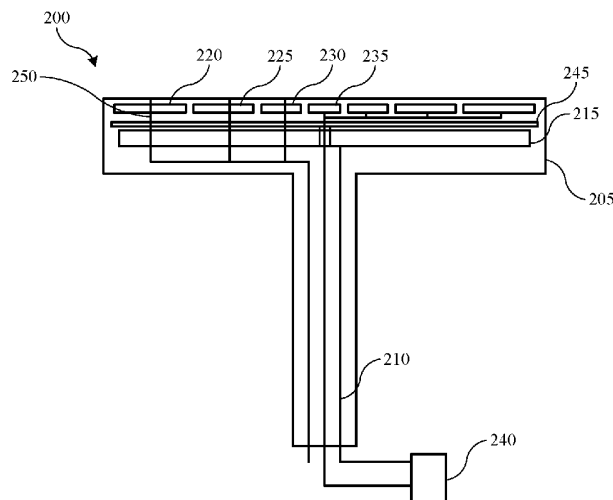


FIG. 2

(57) Abstract: Exemplary semiconductor processing chambers may include a pedestal comprising a platen configured to support a semiconductor substrate across a surface of the platen. The chambers may include a first conductive mesh incorporated within the platen and configured to operate as a first chucking mesh. The first conductive mesh may extend radially across the platen. The chambers may include a second conductive mesh incorporated within the platen and configured to operate as a second chucking mesh. The second conductive mesh may be characterized by an annular shape. The second conductive mesh may be disposed between the first conductive mesh and the surface of the platen.

[Continued on next page]

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